HFZT

A733

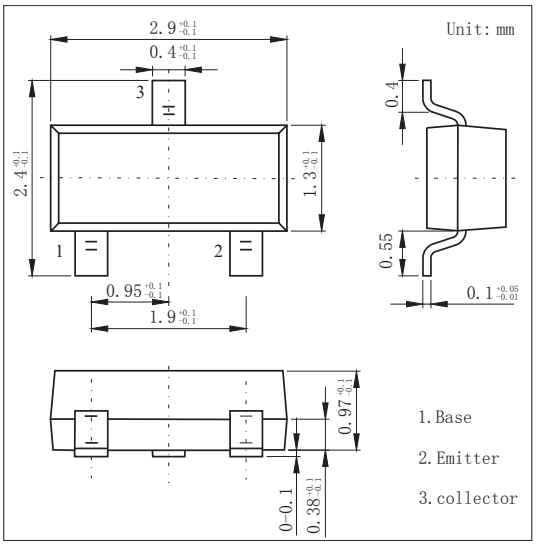
SOT-23 Plastic-Encapsulate Transistors

FEATURES

- Low dynamic output impedance
- The effective temperature compensation in the working range of full temperature
- Low output noise voltage
- Fast on-state response
- PNP Transistors

MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-60	V
Collector to emitter voltage	V_{CEO}	-50	V
Emitter to base voltage	V_{EBO}	-5.0	V
Collector Current (DC)	I_C	-150	mA
Power dissipation	P_C	200	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

Electrical Specification (T_A=25°C unless otherwise specified)

Parameter	Symbol	Testconditi ons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	I_C= -50uA,I_E=0	-60			V
Collector-emitter breakdown voltage	V_{CEO}	I_C= -1mA , I_B=0	-50			V
Emitter-base breakdown voltage	V_{EBO}	I_E= -50uA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}= -60 V , I_E=0			-0.1	uA
Emitter cut-off current	I_{EBO}	V_{EB}= -5 V , I_C=0			-0.1	uA
DC current gain	h_{FE}	V_{CE}= -6 V, I_C=-1mA	120		475	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= -100mA, I_B=- 10mA		-0.18	-0.3	V
Base-emitter voltage	$V_{BE(on)}$	V_{CE}=-6V,I_C=-1.0mA	-0.58	-0.62	-0.68	V
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHZ		4.5	7	pF
Noise figure	NF	V_{CE}=-6V,I_C=-0.3mA,R_g=10kΩ,f=100HZ		6	20	dB
Transition frequency	f_T	V_{CE}=-6V,I_C=-10mA	50			MHz

RATINGS AND CHARACTERISTIC CURVES